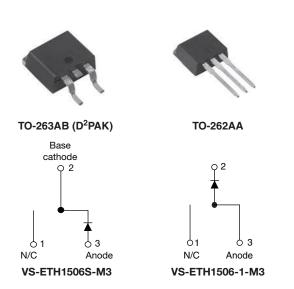


Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt®



PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK), TO-262AA						
I _{F(AV)}	15 A						
V _R	600 V						
V _F at I _F	1.25 V						
t _{rr} (typ.)	21 ns						
T _J max.	175 °C						
Diode variation	Single die						

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912







ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Repetitive peak reverse voltage	V_{RRM}		600	V				
Average rectified forward current	I _{F(AV)}	T _C = 139 °C	15	А				
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	160	A				
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-			
Forward voltage	V _F	I _F = 15A	-	1.8	2.45	V		
		I _F = 15 A, T _J = 150 °C	-	1.25	1.6			
Deverage legisers as surrent	I _R	V _R = V _R rated	-	0.01	15			
Reverse leakage current		T _J = 150 °C, V _R = V _R rated	-	20	200	μA		
Junction capacitance	C _T	V _R = 600 V	-	12	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt =$	100 A/μs, V _R = 30 V	-	21	26			
		I _F = 1.5 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	25	36	no		
	t _{rr}	T _J = 25 °C		-	29	-	ns		
		T _J = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	65	-			
B		T _J = 25 °C		-	3.9	-	A		
Peak recovery current	IRRM	T _J = 125 °C		-	7.0	-			
Deverse vecesses aboves	0	T _J = 25 °C	- VH - 000 V	-	60	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	240	-	110		
Reverse recovery time	t _{rr}		I _F = 15 A	-	42	-	ns		
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 800 A/\mu s$	-	21	-	Α		
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	480	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction to case	R _{thJC}		-	1.3	1.51	°C/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Marking daving		Case style TO-263AB (D ² PAK)	ETH1506SH			•			
Marking device		Case style TO-262		ETH1	506-1H				

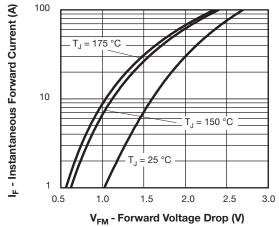


Fig. 1 - Typical Forward Voltage Drop Characteristics

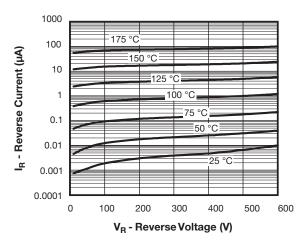


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Vishay Semiconductors

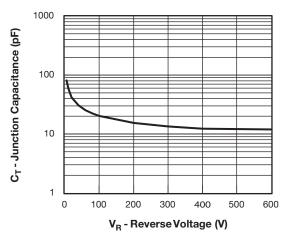


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

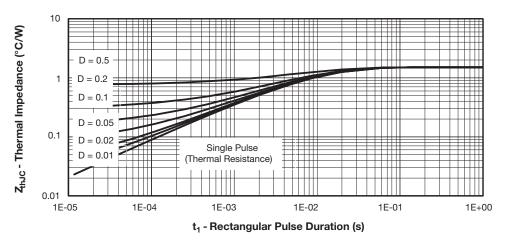


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

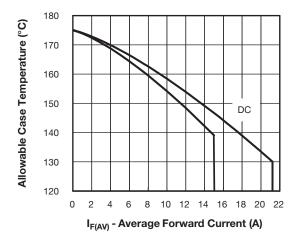


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

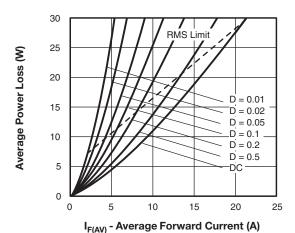


Fig. 6 - Forward Power Loss Characteristics

Vishay Semiconductors

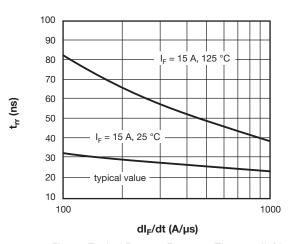


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

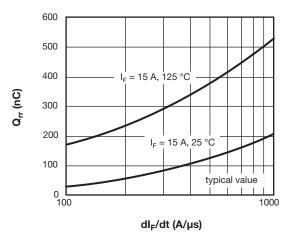


Fig. 8 - Typical Stored Charge vs. dl_F/dt

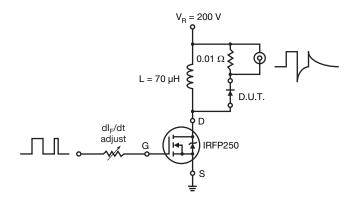
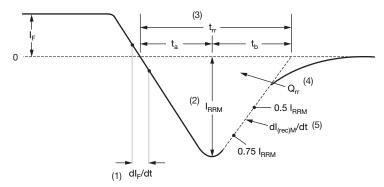


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

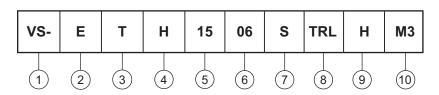
(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Circuit configuration
E = single diode

3 - T = TO-220

4 - H = Hyperfast recovery time

5 - Current code (15 = 15 A)

6 - Voltage code (06 = 600 V)

 $\overline{7}$ - \cdot S = D²PAK

- • -1 = TO-262

8 - • None = tube

- • TRL = tape and reel (left oriented, for D²PAK package)

- • TRR = tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-ETH1506SHM3	50	1000	Antistatic plastic tube				
VS-ETH1506-1HM3	50	1000	Antistatic plastic tube				
VS-ETH1506STRRHM3	800	800	13" diameter reel				
VS-ETH1506STRLHM3	800	800	13" diameter reel				

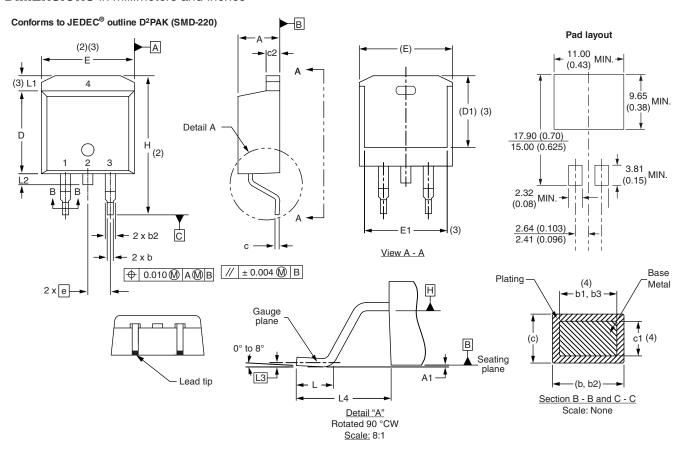
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046				
Differsions	TO-262AA	www.vishay.com/doc?95419				
Part marking information	TO-263AB (D ² PAK)	www.vishay.com/doc?95444				
Fait marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032				



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

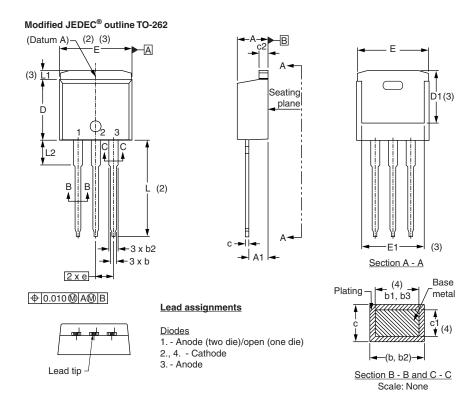
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	METERS	INC	INCHES		
STINIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.36	3.71	0.132	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- 5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

Revision: 11-Jul-2019 1 Document Number: 95419



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)